Elektronische Bauelemente

2SD1468

1A , 30V

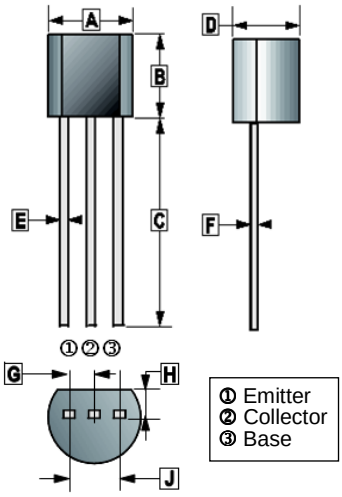
NPN Plastic-Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Low Saturation Voltage
- Ideal for Low Voltage, High Current Dribes
- High DC Current Gain and High Current

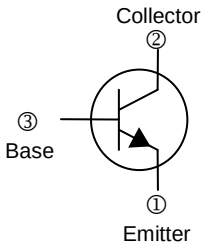
TO-92



REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

CLASSIFICATION OF h_{FE}

Product-Rank	2SD1468-Q	2SD1468-R	2SD1468-S
Range	120~270	180~390	270~560



ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	15	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	1	A
Collector Power Dissipation	P_C	625	W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	30	-	-	V	I_C=50μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	15	-	-	V	I_C=1mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	5	-	-	V	I_E=50μA, I_C=0
Collector Cut – Off Current	I_{CBO}	-	-	0.5	μA	V_{CB}=20V, I_E=0
Emitter Cut – Off Current	I_{EBO}	-	-	0.5	μA	V_{EB}=4V, I_C=0
DC Current Gain	h_{FE}	120	-	560		V_{CE}=3V, I_C=100mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.4	V	I_C=500mA, I_B=50mA
Transition Frequency	f_T	50	-	-	MHz	V_{CE}=5V, I_C=50mA, f=100MHz
Collector Output Capacitance	C_{ob}	-	-	30	pF	V_{CB}=10V, I_E=0, f=1MHz